

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

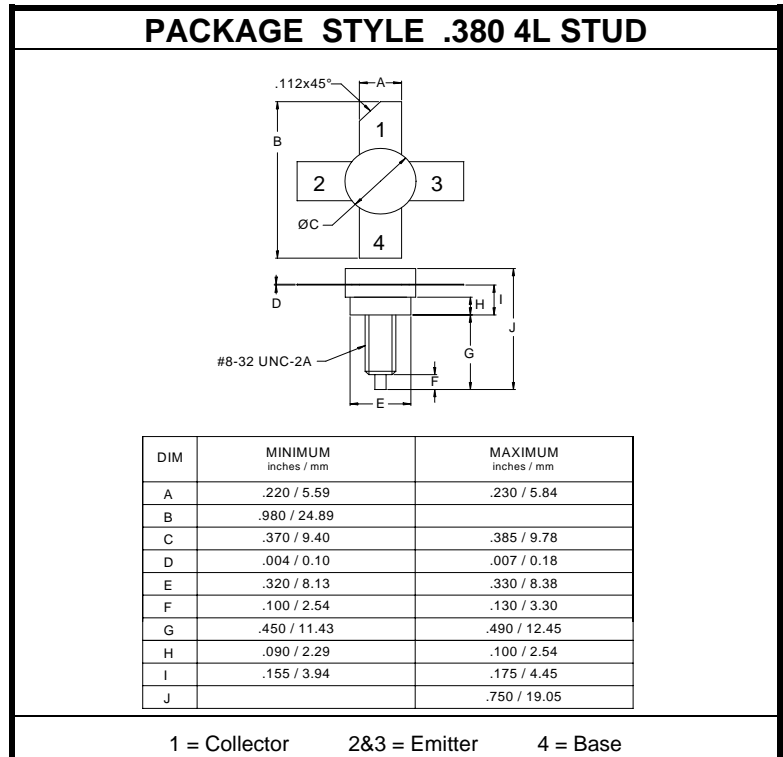
The **ASI BLY92C** is designed for Class C FM amplifier applications up to 250 MHz.

**FEATURES:**

- $P_G = 11$  dB typical at 175 MHz
- High VSWR capability
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	4.0 A
$V_{CB0}$	65 V
$V_{CEO}$	35 V
$V_{EBO}$	4.0 V
$P_{DISS}$	40 W @ $T_C = 25^\circ C$
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	4.4 °C/W


**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CES}$	$I_C = 200$ mA	65			V
$BV_{CEO}$	$I_C = 200$ mA	35			V
$BV_{EBO}$	$I_E = 10$ mA	4.0			V
$I_{CBO}$	$V_{CB} = 30$ V			2.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 200$ mA	10		100	---
$C_{ob}$	$V_{CB} = 30$ V $f = 1.0$ MHz		40	50	pF
$P_G$	$V_{CC} = 28$ V $P_{OUT} = 15$ W $f = 175$ MHz	10	11		dB
$\eta_c$	$P_{IN} = 1.0$ W	50	60		%